

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S3	422	S2 and (relaxed or pseudo-relaxed or pseudo adj relaxed)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/01 16:22
S4	343	S3 and @ad<"20030626"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/01 16:33
S5	10756	((438/458,751,478,149,406,770,10,763) or (257/347,12,19,190)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/05 08:51
S6	423	S5 and (relaxed or pseudo-relaxed or pseudo adj relaxed)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/05 08:51
S7	343	S6 and @ad<"20030626"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/05 08:51
S12	16	S7 and (strained adj2 semiconductor adj2 layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/06 10:20
S13	219	"2002146892", "5882987", "5906951", "6059895", "2002072130", "6524935"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/05 10:26
S14	197	S13 and @ad<"20030626"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/05 10:37

S16	88	S14 and "20030003679", "5461243", "6352942", "20020072130"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/05 10:41
S17	76	S16 and @ad<"20030626"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/08 13:59
S23	10756	((438/458,751,478,149,406,770,10, 763) or (257/347,12,19,190)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/06 09:19
S24	423	S23 and (relaxed or pseudo-relaxed or pseudo adj relaxed)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 08:39
S25	343	S24 and @ad<"20030626"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/06 09:22
S28	12720	((438/458,751,478,149,406,770,10, 763;455,459) or (257/347,12,19, 190,619,620,349)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/06 09:20
S29	468	S28 and (relaxed or pseudo-relaxed or pseudo adj relaxed)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/08 15:03
S30	377	S29 and @ad<"20030626"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/06 09:22

S31	18	S30 and (strained adj2 semiconductor adj2 layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/06 09:23
S32	12720	((438/458,751,478,149,406,770,10,763,455,459) or (257/347,12,19,190,619,620,349)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/06 15:49
S33	468	S32 and (relaxed or pseudo-relaxed or pseudo adj relaxed)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/06 15:49
S34	377	S33 and @ad<"20030626"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/06 15:49
S35	2	S34 and viscous	USPAT	OR	OFF	2005/07/06 15:49
S36	10770	((438/458,751,478,149,406,770,10,763) or (257/347,12,19,190)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 08:41
S37	82	S36 and (compliant adj2 substrate or viscous adj2 flow)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 08:41
S38	73	S37 and @ad<"20030626"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 08:43
S40	62	S38 and bonding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 08:52

S41	7	S38 and (viscous or viscosity adj3 temperature)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 08:53
S42	12738	((438/458,751,478,149,406,770,10,763,455,459) or (257/347,12,19,190,619,620,349)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 14:04
S43	470	S42 and (relaxed or pseudo-relaxed or pseudo adj relaxed)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 14:04
S44	377	S43 and @ad<"20030626"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 14:04
S45	10770	((438/458,751,478,149,406,770,10,763) or (257/347,12,19,190)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 14:14
S46	425	S45 and (relaxed or pseudo-relaxed or pseudo adj relaxed)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 14:14
S47	343	S46 and @ad<"20030626"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 14:14
S48	16	S47 and (strained adj2 semiconductor adj2 layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 14:22

S49	136	ghyselen.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 14:24
S50	77	S49 and @ad<"20030626"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 14:34
S51	5	S50 and (relaxed or pseudo adj2 relaxed or pseudo-realxed)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 14:29
S52	3	S51 and strained	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 14:30
S53	10770	((438/458,751,478,149,406,770,10, 763) or (257/347,12,19,190)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/08 13:38
S54	82	S53 and (compliant adj2 substrate or viscous adj2 flow)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/08 13:38
S55	73	S54 and @ad<"20030626"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/08 13:38
S56	62	S55 and bonding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/08 13:40
S60	4	S56 and separation near layer	USPAT	OR	OFF	2005/07/08 13:50

S61	219	"2002146892", "5882987", "5906951", "6059895", "2002072130", "6524935"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/08 14:05
S62	197	S61 and @ad<"20030626"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/08 14:05
S63	88	S62 and "20030003679", "5461243", "6352942", "20020072130"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/08 14:05
S64	76	S63 and @ad<"20030626"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/08 14:05
S66	56	S64 and (implantation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/08 15:01
S68	12738	((438/458,751,478,149,406,770,10, 763,455,459) or (257/347,12,19, 190,619,620,349)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/08 15:03
S69	11270	S68 and @ad<"20030626"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/08 15:04
S70	54	S69 and (donor adj substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/08 15:06

S71	52	S70 and (implant\$6)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/08 15:07
S72	50	S71 and (separation or detach\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 15:17
S77	6319	S68 and @ad<"20030626"	USPAT	OR	OFF	2005/07/08 15:31
S78	1888	S77 and (SOI)	USPAT	OR	ON	2005/07/08 15:32
S79	28	S78 and (insulation near layer near thickness)	USPAT	OR	ON	2005/07/08 15:33